

WBFBP-03D Plastic-Encapsulate Diodes

DK914LLD03 SWITCHING DIODE

DESCRIPTION

Epitaxial planar silicon diode

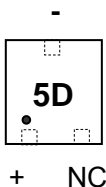
FEATURES

Fast Switching Speed
Ultra-Small Surface Mount Package
For General Purpose Switching Applications
High Conductance
Lead Free Product

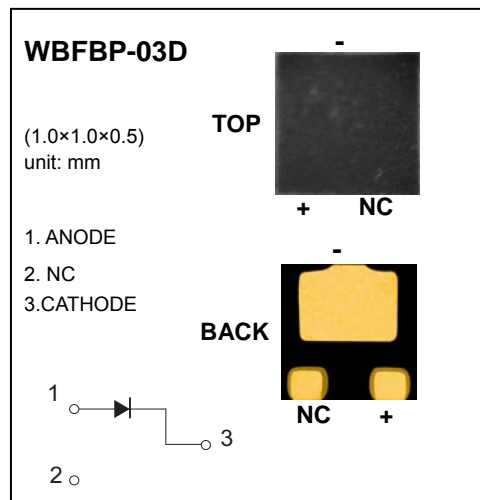
APPLICATION

High Conductance Ultra Fast Diode
For Portable Equipment:(i.e. Mobile Phone,MP3, MD,CD-ROM,
DVD-ROM, Note Book PC, etc.)

MARKING: 5D



+ NC



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	500	mA
Average Rectified Output Current	I_O	300	mA
Power Dissipation	P_D	100	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V _{F1}			0.715	V	I _F =1mA
	V _{F2}			0.855	V	I _F =10mA
	V _{F3}			1.0	V	I _F =50mA
	V _{F4}			1.25	V	I _F =150mA
Reverse current	I _{R1}			1	μA	V _R =75V
	I _{R2}			25	nA	V _R =20V
Capacitance between terminals	C _T			2	pF	V _R =0, f=1MHz
Reverse recovery time	t _{rr}			4	ns	I _F =I _R =10mA, I _{rr} =0.1I _R